

KT602B Datasheet, Equivalent, Cross Reference Search

Type Designator: KT602B

Material of Transistor: Si

Polarity: NPN

Maximum Collector Power Dissipation (P_c): 2.8 W

Maximum Collector-Base Voltage $|V_{cb}|$: 120 V

Maximum Collector-Emitter Voltage $|V_{ce}|$: 100 V

Maximum Emitter-Base Voltage $|V_{eb}|$: 5 V

Maximum Collector Current $|I_c \text{ max}|$: 0.075 A

Max. Operating Junction Temperature (T_j): 150 °C

Transition Frequency (f_t): 150 MHz

Collector Capacitance (C_c): 4 pF

Forward Current Transfer Ratio (h_{FE}), MIN: 50

Noise Figure, dB: -